K Vedam

List of Publications by Year
in descending order

154	4,308	94269	143772
papers	citations	37 h-index	57 g-index

163	163	163	1771
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Spectroscopic ellipsometry: a historical overview. Thin Solid Films, 1998, 313-314, 1-9.	0.8	145
2	Ion-implantation induced anomalous surface amorphization in silicon. Nuclear Instruments & Methods in Physics Research B, 1994, 85, 335-339.	0.6	34
3	Characterization of inhomogeneous transparent thin films on transparent substrates by spectroscopic ellipsometry: refractive indices n(Î») of some fluoride coating materials. Applied Optics, 1994, 33, 2664.	2.1	29
4	Optical Characterization of Inhomogeneous Transparent Films on Transparent Substrates by Spectroscopic Ellipsometry. Physics of Thin Films, 1994, , 191-247.	1.1	20
5	Characterization of Ferroelectric Films by Spectroscopic Ellipsometry. Physics of Thin Films, 1994, , 249-278.	1.1	2
6	Ion-implantation-caused special damage profiles determined by spectroscopic ellipsometry in crystalline and in relaxed (annealed) amorphous silicon. Thin Solid Films, 1993, 233, 117-121.	0.8	9
7	Hydrogen diffusion and reaction processes in thin films investigated by real time spectroscopic ellipsometry. Thin Solid Films, 1993, 233, 276-280.	0.8	9
8	Spectroscopic ellipsometry studies on ion beam sputter deposited Pb(Zr, Ti)O3 films on sapphire and Pt-coated silicon substrates. Thin Solid Films, 1993, 230, 15-27.	0.8	47
9	Studies on inhomogeneous transparent optical coatings on transparent substrates by spectroscopic ellipsometry. Thin Solid Films, 1993, 234, 439-442.	0.8	17
10	Determination of the optical function n(Î») of vitreous silica by spectroscopic ellipsometry with an achromatic compensator. Applied Optics, 1993, 32, 6391.	2.1	26
11	Effect of preparation conditions on the morphology and electrochromic properties of amorphous tungsten oxide films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1993, 11, 1881-1887.	0.9	47
12	Monitoring ion etching of GaAs/AlGaAs heterostructures by real time spectroscopic ellipsometry: Determination of layer thicknesses, compositions, and surface temperature. Applied Physics Letters, 1992, 60, 2776-2778.	1.5	19
13	Real time spectroscopic ellipsometry characterization of the nucleation of diamond by filamentâ€assisted chemical vapor deposition. Journal of Applied Physics, 1992, 71, 5287-5289.	1.1	29
14	Determination of the optical constants of an inhomogeneous transparent LaF_3 thin film on a transparent substrate by spectroscopic ellipsometry. Optics Letters, 1992, 17, 538.	1.7	29
15	Comparative study of the effect of annealing of nitrogen-implanted silicon-on-insulator structures by spectroscopic ellipsometry, cross-sectional transmission electron microscopy and Rutherford backscattering spectroscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1992, 12, 177-184.	1.7	8
16	Real Time Spectroscopic Ellipsometry: In Situ Characterization of Pyrrole Electropolymerization. Journal of the Electrochemical Society, 1991, 138, 3266-3275.	1.3	63
17	Temperature dependence of optical constants of MoS_2 for pyrooptical devices. Applied Optics, 1991, 30, 1583.	2.1	3
18	Optical characterization of a four-medium thin film structure by real time spectroscopic ellipsometry: amorphous carbon on tantalum. Applied Optics, 1991, 30, 2692.	2.1	41

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19	Morphology Control Of The Electrochromic Effect In Tungsten Oxide Thin Films. Materials Research Society Symposia Proceedings, 1991, 255, 275.	0.1	4
20	Real time monitoring of filament-assisted chemically vapor deposited diamond by spectroscopic ellipsometry. Surface and Coatings Technology, 1991, 49, 381-386.	2.2	11
21	Ion beam etching of GaAs and GaAs/AlGaAs heterostructures probed in real time by spectroscopic ellipsometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 810-815.	0.9	18
22	Characterization of ion beamâ€induced surface modification of diamond films by real time spectroscopic ellipsometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1991, 9, 1123-1128.	0.9	21
23	Real time monitoring of filament-assisted chemically vapor deposited diamond by spectroscopic ellipsometry. , 1991, , 381-386.		0
24	Real-time spectroscopic ellipsometry study of theelectrochemical deposition of polypyrrole thin films. Thin Solid Films, 1990, 193-194, 350-360.	0.8	15
25	Real-time spectroscopic ellipsometry for determination of the optical functions of ion-beam-deposited hydrogenated amorphous carbon. Thin Solid Films, 1990, 193-194, 361-370.	0.8	5
26	Spectroscopic ellipsometry studies of crystalline silicon implanted with carbon ions. Journal of Applied Physics, 1990, 67, 3555-3559.	1.1	30
27	Characterization of the interface between Ge+â€implanted crystalline silicon and its thermally grown oxide by spectroscopic ellipsometry. Journal of Applied Physics, 1990, 67, 599-603.	1.1	18
28	Fast scanning spectroelectrochemical ellipsometry: In-situ characterization of gold oxide. Surface Science, 1990, 233, 341-350.	0.8	74
29	Thinâ€film deposition by a new laser ablation and plasma hybrid technique. Applied Physics Letters, 1989, 54, 2455-2457.	1.5	121
30	Real-time and spectroscopic ellipsometry characterizatio of diamond and diamond-like carbon. Thin Solid Films, 1989, 181, 565-578.	0.8	30
31	Simultaneous determination of refractive index, its dispersion and depth-profile of magnesium oxide thin film by spectroscopic ellipsometry. Applied Optics, 1989, 28, 2691.	2.1	33
32	Simultaneous determination of dispersion relation and depth profile of thorium fluoride thin film by spectroscopic ellipsometry. Thin Solid Films, 1988, 166, 325-334.	0.8	38
33	High-dose carbon ion implantation studies in silicon. Thin Solid Films, 1988, 163, 323-329.	0.8	16
34	Spectroscopic ellipsometry of amorphous Ni0.95Tb0.05 and crystalline nickel. Materials Science and Engineering, 1988, 99, 281-283.	0.1	4
35	Investigation of the void structure in amorphous germanium thin films as a function of lowâ€energy ion bombardment. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 1631-1635.	0.9	86
36	Spectroscopic ellipsometry of sputtered amorphousNi0.95Tb0.05and crystalline Ni. Physical Review B, 1988, 38, 1562-1565.	1.1	3

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37	SIMULTANEOUS DETERMINATION OF DISPERSION RELATION AND DEPTH PROFILE OF THORIUM FLUORIDE THIN FILM BY SPECTROSCOPIC ELLIPSOMETRY. , 1988, , 325-334.		0
38	Processing & Characterization Of Thin Films Of SiO 2 On Si For Integrated Circuits. , 1988, 0945, 84.		1
39	Intrinsic Stress in a-Germanium Films Deposited by RF-Magnetron Sputtering. Materials Research Society Symposia Proceedings, 1988, 130, 355.	0.1	9
40	Nondestructive Depth-Profiling of Multilayer Structures by Spectroscopic Ellipsometry. MRS Bulletin, 1987, 12, 21-23.	1.7	10
41	Formation and nondestructive characterization of ion implanted siliconâ€onâ€insulator layers. Applied Physics Letters, 1987, 51, 343-345.	1.5	35
42	Thickness dependence of optical gap and void fraction for sputtered amorphous germanium. Physical Review B, 1987, 35, 9368-9371.	1.1	41
43	Nonuniformity in void concentration between the initial and final growth stage of sputtereda-Ge films studied using spectroscopic ellipsometry. Physical Review B, 1987, 36, 6206-6208.	1.1	7
44	Electrical, Optical and Structural Properties of Thin SiO2 Films On Si. Materials Research Society Symposia Proceedings, 1987, 105, 169.	0.1	4
45	High Dose Carbon Ion Implantation Studies in Silicon. Materials Research Society Symposia Proceedings, 1987, 107, 483.	0.1	1
46	Formation And Nondestructive Characterization Of Ion Implanted Soi Layers. Proceedings of SPIE, 1987, 0797, 77.	0.8	0
47	Nondestructive depth profiling of ZnS and MgO films by spectroscopic ellipsometry. Optics Letters, 1987, 12, 456.	1.7	26
48	Analytic solution of the pseudo-Brewster angle. Journal of the Optical Society of America A: Optics and Image Science, and Vision, 1986, 3, 1772.	0.8	43
49	Proper choice of the error function in modeling spectroellipsometric data. Applied Optics, 1986, 25, 2013.	2.1	37
50	Density of amorphous germanium films by spectroscopic ellipsometry. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1986, 4, 577-582.	0.9	41
51	Spectroscopic ellipsometry study of glowâ€dischargeâ€deposited thin films ofaâ€Ge:H. Journal of Applied Physics, 1986, 60, 3724-3731.	1.1	22
52	Spectroscopic ellipsometry: A new tool for nondestructive depth profiling and characterization of interfaces. Journal of Applied Physics, 1986, 59, 694-701.	1.1	113
53	Thicknessâ€dependent void fraction of rfâ€sputtered amorphous Ge films by spectroscopic ellipsometry. Applied Physics Letters, 1986, 49, 328-330.	1.5	26
54	Surface Roughness Characterization of al Films by Spectroscopic Ellipsometry. Materials Research Society Symposia Proceedings, 1985, 54, 669.	0.1	1

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55	Supersensitive Dial-Gage Measurement by Observing Rotation of Laser Speckles. Experimental Techniques, 1985, 9, 16-17.	0.9	1
56	Ar ion beam and CCl4reactive ion etching: A comparison of etching damage and of damage passivation by hydrogen. Journal of Applied Physics, 1985, 58, 4282-4291.	1.1	22
57	Nondestructive depth profiling by spectroscopic ellipsometry. Applied Physics Letters, 1985, 47, 339-341.	1.5	135
58	Roughness measurements by spectroscopic ellipsometry. Applied Optics, 1985, 24, 3773.	2.1	39
59	Pressure dependence of the refractive index and dielectric constant in a fluoroperovskite, KMgF3. Physical Review B, 1984, 29, 6921-6925.	1.1	23
60	Electrical characteristics of r.f.-sputtered CdTe thin-films for photovoltaic applications. Solid-State Electronics, 1984, 27, 329-337.	0.8	22
61	Spectroscopic Ellipsometry Study of rf-Sputtered a-Ge Films. Materials Research Society Symposia Proceedings, 1984, 38, 301.	0.1	7
62	Refractive index of liquids at high pressures. Critical Reviews in Solid State and Materials Sciences, 1983, 11, 1-45.	6.8	21
63	Complete 3-D deformation analysis in the white light speckle method. Applied Optics, 1983, 22, 213.	2.1	4
64	Processing speckle photography data: circular imaging aperture. Applied Optics, 1983, 22, 653.	2.1	18
65	Selective counting path of Young's fringes in speckle photography for eliminating diffraction halo effects. Applied Optics, 1983, 22, 2242.	2.1	14
66	Characterization of Ion Implanted Silicon by Spectroscopic Ellipsometry and Cross Section Transmission Electron Microscopy. Materials Research Society Symposia Proceedings, 1983, 27, 299.	0.1	3
67	The Study of Damage Profile of Ion Implanted Layer on Si by Spectroscopic Ellipsometry. Materials Research Society Symposia Proceedings, 1982, 14, 529.	0.1	3
68	Importance of using Eulerian representation of strain in high pressure studies on liquids. Journal of Chemical Physics, 1982, 77, 1461-1463.	1.2	19
69	Direct observation of laser speckles for real-time analysis of lateral motions. Optics Letters, 1981, 6, 511.	1.7	5
70	Stress-optic coefficient of ZnSe at 106 Î¼m. Applied Optics, 1981, 20, 2878.	2.1	6
71	Speckle photography of lateral sinusoidal vibrations: error due to varying halo intensity. Applied Optics, 1981, 20, 3388.	2.1	17
72	Explosive crystallization of rf-sputtered amorphous CdTe films. Journal of Electronic Materials, 1981, 10, 433-443.	1.0	23

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73	Piezoâ€•and thermoâ€•optic behavior of LiTaO3. Journal of Applied Physics, 1981, 52, 944-947.	1.1	11
74	Characterization of surfaces of laser-annealed samples by ellipsometry. Surface Science, 1980, 96, 319-328.	0.8	3
75	Laser speckle photography for supersensitive dial gauge. Optics Letters, 1980, 5, 441.	1.7	3
76	Piezoâ€•and elastoâ€•optic properties of liquids under high pressure. III. Results on twelve more liquids. Journal of Chemical Physics, 1980, 73, 4577-4584.	1.2	25
77	Piezoâ€•and elastoâ€•optic properties of deuterium oxide under high pressure. Journal of Chemical Physics, 1980, 72, 1410-1411.	1.2	1
78	Application of fringe shifting technique in speckle photography. Pramana - Journal of Physics, 1979, 12, 341-346.	0.9	2
79	A critical evaluation of equations of state by piezoâ€•optic measurements. Journal of Applied Physics, 1979, 50, 1328-1333.	1.1	8
80	Increasing effective size of holography tables. Applied Optics, 1979, 18, 418_1.	2.1	0
81	Testing the trueness of circular surfaces: a simple holographic method. Applied Optics, 1979, 18, 627.	2.1	1
82	Testing the trueness of circular surfaces by laser speckle photography. Applied Optics, 1979, 18, 2351.	2.1	2
83	Ordinary paper for position determination of intense laser pulse. Applied Optics, 1979, 18, 4063.	2.1	1
84	Measurement of subspeckle-size changes by laser-speckle photography. Optics Letters, 1979, 4, 406.	1.7	8
85	Piezo-Optic Behavior and the Equation of State of Liquids. , 1979, , 421-427.		0
86	Piezoâ€•and elastoâ€•optic properties of liquids under high pressure. II. Refractive index vs density. Journal of Chemical Physics, 1978, 69, 4772-4778.	1.2	71
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88	Unusual white light conoscopic figure in single crystal lithium metagermanate Li_2GeO_3. Applied Optics, 1978, 17, 3339_1.	2.1	3
89	Retroreflection from spherical glass beads in highway pavement markings 1: Specular reflection. Applied Optics, 1978, 17, 1855.	2.1	18
90	Retroreflection from spherical glass beads in highway pavement markings 2: Diffuse reflection (a first) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	2.1	20

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91	The Pressure Dependence of the Magnetic Susceptibility of Rare-Earth Substituted Samarium Sulfide. , 1978, , 187-204.		0
92	Optical interferometry in liquids at high pressures to 14 kilobars. Review of Scientific Instruments, 1977, 48, 245-246.	0.6	21
93	Ellipsometric studies of environmentâ€sensitive polish layers of glass. Journal of Applied Physics, 1977, 48, 1155-1157.	1.1	14
94	Variation of refractive index of polystyrene with pressure to 7 kbar. Journal of Applied Physics, 1976, 47, 2443-2446.	1.1	5
95	Generalized ellipsometric method for the determination of all the optical constants of the system: Optically absorbing film on an absorbing substrate. Surface Science, 1976, 56, 49-63.	0.8	26
96	Characterization of defects in real surfaces by ellipsometry. Surface Science, 1976, 56, 221-236.	0.8	22
97	Support for rebuttals. Physics Today, 1976, 29, 43-43.	0.3	0
98	Piezo- and thermo-optic behavior of spinel (MgAl2O4). Journal of Solid State Chemistry, 1975, 12, 213-218.	1.4	18
99	Piezo-optic Behavior of Water and Carbon Tetrachloride under High Pressure. Physical Review Letters, 1975, 35, 1014-1016.	2.9	20
100	Dispersion of the Elasto-Optic Constants of Potassium Halides. , 1975, , 169-177.		5
101	Characterization of real surfaces of vitreous silica by ellipsometry. Materials Research Bulletin, 1974, 9, 1503-1509.	2.7	20
102	Growth of color centres and hardening of CaF2 by heavy dose of Î³-irradiation. Physica Status Solidi A, 1973, 19, 625-634.	1.7	5
103	OPTICAL STUDIES ON THE HIGH PRESSURE PHASE TRANSFORMATIONS IN SILVER IODIDE SINGLE CRYSTALS. , 1973, , 91-99.		2
104	Nonlinear variation of the induced birefringence of vitreous silica with uniaxial stress to 7 kbar. Journal of Applied Physics, 1972, 43, 3724-3728.	1.1	6
105	Variation of the refractive index of boric oxide glasses with hydrostatic pressure to 7 kbar. Journal of Applied Physics, 1972, 43, 3623-3627.	1.1	13
106	Hardening of CaF2 singleâ€crystal surfaces due to contamination by atmospheric oxygen. Journal of Applied Physics, 1972, 43, 4396-4400.	1.1	4
107	Direct Optical Observation of the Semiconductor-to-Metal Transition in SmS under Pressure. Physical Review B, 1972, 6, 3023-3026.	1.1	78
108	Generalized Ellipsometric Method for the Absorbing Substrate Covered with a Transparent-Film System Optical Constants of Silicon at 3655 Ã...*. Journal of the Optical Society of America, 1972, 62, 16.	1.2	47

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109	Optical Constants of Silicon at 5461 Ã...*. Journal of the Optical Society of America, 1972, 62, 596.	1.2	12
110	Characterization of real surfaces by ellipsometry. Surface Science, 1972, 29, 379-395.	0.8	57
111	Piezo-optic behavior of forsterite, Mg2SiO4. Journal of Physics and Chemistry of Solids, 1972, 33, 1251-1255.	1.9	14
112	Characterisation of thin surface films on germanium in various solvents by ellipsometry. Journal of Materials Science, 1971, 6, 969-973.	1.7	9
113	Electroreflectance in GeSi alloys under hydrostatic pressure. Solid State Communications, 1971, 9, 1187-1191.	0.9	39
114	Optical Anisotropy of Silicon Single Crystals. Physical Review B, 1971, 3, 2567-2571.	1.1	87
115	Epitaxial Growth of Ice Crystals on the Muscovite Cleavage Plane and Their Relation to Partial Dislocations. Journal of Applied Physics, 1971, 42, 516-520.	1.1	23
116	The study of dislocations in muscovite mica by X-ray transmission topography. Philosophical Magazine and Journal, 1970, 22, 255-268.	1.8	10
117	Finite size effects on lattice vibrations of ionic crystals and measurements of infrared absorption spectra. Physica Status Solidi A, 1970, 3, 647-656.	1.7	13
118	Examination of Imperfect Muscovite Crystals by Xâ€Ray Diffraction Methods. Journal of Applied Physics, 1970, 41, 50-53.	1.1	15
119	Piezo-Optic Properties of Amorphous Selenium at a Wavelength of 115 Î¼. Journal of the Optical Society of America, 1970, 60, 800.	1.2	16
120	Nonlinear Piezo-Optic Behavior of Sphalerite (Î±â˜ZnS). Physical Review, 1969, 177, 1394-1394.	2.7	1
121	Pressure Dependence of the Refractive Indices of the Hexagonal Crystals Beryl,Î±-CdS,Î±-ZnS, and ZnO. Physical Review, 1969, 181, 1196-1201.	2.7	60
122	THIN FILM CHARACTERIZATION BY ELECTRON MICROPROBE AND ELLIPSOMETRY: SiO2FILMS ON SILICON. Applied Physics Letters, 1969, 14, 43-45.	1.5	8
123	Variation of the refractive indices of KBr and KI with pressure to 14 kbars. Materials Research Bulletin, 1969, 4, 573-579.	2.7	30
124	Optical constants of germanium by ellipsometry. Physics Letters, Section A: General, Atomic and Solid State Physics, 1969, 29, 428-429.	0.9	6
125	Ellipsometric Method for the Determination of All the Optical Parameters of the System of an Isotropic Nonabsorbing Film on an Isotropic Absorbing Substrate Optical Constants of Silicon*. Journal of the Optical Society of America, 1969, 59, 64.	1.2	51
126	Variation of the refractive indices of calcite, with pressure to 7 kbar. Physica Status Solidi (B): Basic Research, 1968, 26, 285-290.	0.7	10

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128	Pressure Dependence of the Refractive Indices of the Tetragonal Crystals: ADP, KDP, CaMoO_4, CaWO_4, and Rutile*. Journal of the Optical Society of America, 1968, 58, 1446.	1.2	50
129	PIEZOâ€•AND THERMOâ€OPTIC BEHAVIOR OF LiNBO3. Applied Physics Letters, 1968, 12, 138-140.	1.5	11
130	Photoelastic Properties of Sapphire (Î±â€Al2O3). Journal of Applied Physics, 1967, 38, 4555-4556.	1.1	26
131	Nonlinear Variation of the Refractive Indices of Î±-Quartz with Pressure*. Journal of the Optical Society of America, 1967, 57, 1140.	1.2	42
132	Non-linear piezo-optics. Acta Crystallographica, 1967, 22, 630-634.	0.5	19
133	Elastic Constants of Selenium in the Hexagonal and Glassy Phases. Journal of Applied Physics, 1966, 37, 3432-3434.	1.1	51
134	Variation of Refractive Index of MgO with Pressure to 7 kbar. Physical Review, 1966, 146, 548-554.	2.7	88
135	Piezo-optic behaviour of rubidium chloride up to the phase transition point. Journal of Materials Science, 1966, 1, 310-312.	1.7	14
136	Variation of the refractive indices of CaF2, BaF2 and Î²-PbF2 with pressure to 7 kb. Journal of Physics and Chemistry of Solids, 1966, 27, 1563-1566.	1.9	71
137	Nonlinear Variation of Refractive Index of Vitreous Silica with Pressure to 7 Kbars. Journal of the American Ceramic Society, 1966, 49, 531-535.	1.9	51
138	The Laser as a Light Source for Ultramicroscopy and Light Scattering by Imperfections in Crystals. Investigation of Imperfections in LiF, MgO, and Ruby. Journal of Applied Physics, 1966, 37, 2551-2557.	1.1	33
139	Nonlinear Piezo-Optic Behavior of Sphalerite (Î±-ZnS). Physical Review, 1966, 150, 766-767.	2.7	21
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142	Ferroelectric Transition in Rubidium Bisulfate. Physical Review, 1960, 117, 1502-1503.	2.7	89
143	LiH3(SeO3)2: New Room-Temperature Ferroelectric. Physical Review, 1959, 114, 1217-1218.	2.7	85
144	Non-isomorphism of ferroelectric phases of ammonium sulfate and ammonium fluoberyllate. Acta Crystallographica, 1958, 11, 307-307.	0.5	40

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146	Room-Temperature Ferroelectricity in Lithium Hydrazinium Sulfate, Li (N2H5)SO4. Physical Review, 1958, 111, 1467-1468.	2.7	78
147	Dielectric and Thermal Study of(NH4)2SO4and(NH4)2BeF4Transitions. Physical Review, 1958, 112, 405-412.	2.7	193
148	Ferroelectricity in Di-Glycine Nitrate(NH2CH2COOH)2Â·HNO3. Physical Review, 1958, 111, 430-432.	2.7	94
149	New Room-Temperature Ferroelectric. Physical Review, 1958, 110, 1309-1311.	2.7	46
150	Photoelastic properties of barite. Proceedings of the Indian Academy of Sciences - Section A, 1951, 34, 161.	0.2	7
151	Photoelastic constants of sodium chlorate from ultrasonic diffraction. Proceedings of the Indian Academy of Sciences - Section A, 1951, 34, 240.	0.2	6
152	Elastic and photoelastic properties of some optical glasses. Proceedings of the Indian Academy of Sciences - Section A, 1950, 31, 450-458.	0.2	14
153	The Elastic and Photoelastic Constants of Fused Quartz. Physical Review, 1950, 78, 472-473.	2.7	29
154	5.2.2.5 Trigonal system: Classes 3m (C{3v}), 32 (D{3}), (-3)m (D{3d}). , 0, , 59-62.		0